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Addition/Correction
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Correction to Tailoring the Interface Quality between HfO_2 and GaAs via in Situ ZnO Passivation Using Atomic Layer Deposition

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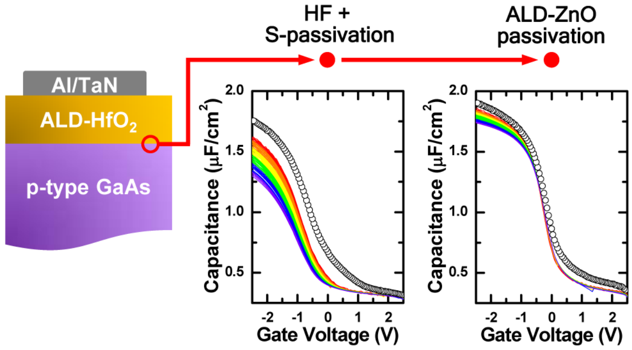
Recently, we found that the table of contents (TOC)/abstract graphic was mistakenly uploaded. The capacitance−voltage curves of the ALD-ZnO passivated sample in the earlier TOC/abstract graphic do not match with Figure 5c. The correct version of TOC/abstract graphic is shown below. The conclusions of the paper are not affected by this change.



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